

GCMS1P4B120S4B1

QSiC™ 1200V SiC Half-Bridge Module

V_{DS}	1200 V
$R_{DS,on}$	1.4 mΩ
$I_D (T_C=25°C)$	813 A
$T_{J,max}$	175°C

Features

- 62mm x 152mm industry standard footprint
- High speed switching SiC MOSFETs
- Freewheeling SiC SBD with zero reverse recovery
- All parts tested to greater than 1,350V
- Kelvin reference for stable operation

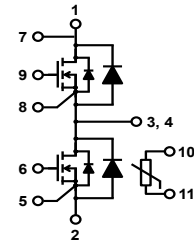
Benefits

- Low switching losses
- Low junction to case thermal resistance
- Very rugged and easy mounting
- Direct mounting to heatsink (isolated package)
- Lower Q_{RR} at high temperature

Applications

- Motor drives
- EV applications
- Smart-grid
- Uninterruptible power supply (UPS)

Package



Part #	Package	Marking
GCMS1P4B120S4B1	S4	GCMS1P4B120S4B1



Absolute Maximum Ratings, at $T_J=25°C$, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit
Drain-Source Voltage	V_{rated}	$V_{GS}=0V, I_{DS}=1000\mu A$	1200	V
Continuous Drain Current	I_{DS}	$T_C=25°C, V_{GS}=18V, T_J=175°C$	813	A
		$T_C=65°C, V_{GS}=18V, T_J=175°C$	699	
Body Diode Drain Current	I_{SD}	$T_C=25°C, V_{GS}=-4.5V, T_J=175°C$	664	
Pulsed Drain Current	$I_{DS,pulse}$	$T_C=25°C, V_{GS}=18V$	2000	
Gate Source Voltage	V_{GSmax}		-8/22	V
	V_{GSop}	Recommended operational	-4.5/18	
Power Dissipation	P_{tot}	$T_C=25°C, T_J=175°C$	1667	W
Junction Temperature	T_J	Continuous	-40...175	°C
Case & Storage Temperature	$T_C, T_{storage}$	Continuous	-40...150	°C

Static Electrical Characteristics, at T_J=25°C, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =10mA	1200	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V	-	0.01	1.0	mA
		V _{DS} =1200V, V _{GS} =0V, T _J =150°C	-	0.23	17	
Gate-Source Leakage Current	I _{GSS+}	V _{GS} =22V, V _{DS} =0V	-	100	2000	nA
	I _{GSS-}	V _{GS} =-8V, V _{DS} =0V	-	-100	-2000	
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _{DS} =200mA	1.8	2.7	4	V
		V _{GS} =V _{DS} , I _{DS} =200mA, T _J =150°C	-	1.9	-	
Drain-Source On-Resistance	R _{DS(on)} *	V _{GS} =18V, I _{DS} =500A	-	1.4	2.3	mΩ
		V _{GS} =18V, I _{DS} =500A, T _J =150°C	-	2.3	-	
Transconductance	g _{fs}	V _{DS} =20V, I _{DS} =500A	-	155	-	S
		V _{DS} =20V, I _{DS} =500A, T _J =150°C	-	177	-	
Internal Gate Resistance	R _{G(int)}	f=1MHz, V _{AC} =25mV, D-S Short, including internal 0.36 ohm series gate resistor**	-	0.7	-	Ω

*R_{DS(on)} measured at kelvin and sense pins (pin #7-8 and pin #8-5), typical 1.4Ωm chip only

**Internal series gate resistor limits maximum switching frequency defined by Figure 35

AC Electrical Characteristics, at T_J=25°C, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =800V, f=100kHz, V _{AC} =25mV	-	84	-	nF
Output Capacitance	C _{OSS}		-	4.01	-	
Reverse Transfer Capacitance	C _{RSS}		-	0.15	-	
Coss Stored Energy	E _{OSS} ***		-	1617	-	
Turn-On Switching Energy	E _{ON}	T _J =25°C	-	7.9	-	mJ
		T _J =125°C	-	7.2	-	
		T _J =150°C	-	7.1	-	
Turn-Off Switching Energy	E _{OFF}	T _J =25°C	-	11.0	-	
		T _J =125°C	-	11.7	-	
		T _J =150°C	-	12.0	-	
Turn-On Delay Time	t _{D(on)}	V _{DD} =600V, I _{DS} =500A, R _{G(ext)} =1Ω, V _{GS} =-4.5/+18V, L=8.9μH,	-	91	-	ns
Rise Time	t _R		-	44	-	
Turn-Off Delay Time	t _{D(off)}		-	216	-	
Fall Time	t _F		-	84	-	
Total Gate Charge	Q _G		-	2595	-	
Gate to Source Charge	Q _{GS}	V _{DD} =800V, I _{DS} =500A, V _{GS} =-4.5/+18V	-	790	-	nC
Gate to Drain Charge	Q _{GD}	-	362	-		

***E_{OSS} is calculated from C_{OSS} curve

Freewheeling Diode Characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode Forward Voltage	V_{SD}	$V_{GS}=-5\text{V}, I_{SD}=500\text{A}$	-	1.5	1.9	V
		$V_{GS}=-5\text{V}, I_{SD}=500\text{A}, T_j=150^\circ\text{C}$	-	2.1	-	
Reverse Recovery Time	t_{RR}	$T_j=25^\circ\text{C}$ $I_S=500\text{A},$ $V_R=600\text{V},$ $V_{GS}=-4.5\text{V},$ $di/dt=12.3\text{A/ns}$	-	20	-	ns
Reverse Recovery Charge	Q_{RR}		-	1.7	-	μC
Peak Reverse Recovery Current	I_{RRM}		-	119	-	A
Reverse Recovery Energy	E_{RR}	$T_j=25^\circ\text{C}$	-	0.62	-	mJ
		$T_j=125^\circ\text{C}$	-	0.87	-	
		$T_j=150^\circ\text{C}$	-	0.91	-	

Thermal and Package Characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction-case	$R_{thJC,MOSFET}$		-	0.081	0.090	$^\circ\text{C/W}$
	$R_{thJC,DIODE}$		-	0.085	0.093	
Thermal resistance, junction-heatsink	$R_{thJH,MOSFET}$	Thermal grease, Thickness=75 μm , $k = 4.0 \text{ W/mK}$	-	0.098	-	$^\circ\text{C/W}$
	$R_{thJH,DIODE}$		-	0.100	-	
Material of module baseplate	-		-	Cu	-	-
Creepage distance	d_{Creep}	terminal to heatsink	-	14.5	-	mm
	d_{Creep}	terminal to terminal	-	13.0	-	mm
Clearance	d_{Clear}	terminal to heatsink	-	12.5	-	mm
	d_{Clear}	terminal to terminal	-	10.0	-	mm
Comparative tracking index	CTI		250	-	400	-
Mounting torque	M_d	M5-0.8 screws	3	-	6	N-m
Terminal connection torque	M_{dt}	M6-1.0 screws	3	-	6	N-m
Package weight	W_t		-	382	-	g
Isolation voltage	V_{ISOL}	$I_{ISOL} < 1\text{mA}, 50/60 \text{ Hz}, 1 \text{ min}$	3400	-	-	V

NTC Characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Rated resistance	R_{NTC}	$T_{NTC} = 25^\circ\text{C}$	-	5.0	-	k Ω
Resistance tolerance	$\Delta R/R$		-5	-	5	%
Beta Value ($T_2 = 50^\circ\text{C}$)	$\beta_{25/50}$	$R_2 = R_{25} \cdot \exp [B_{25/50} (1/T_2 - 1/(298,15 \text{ K}))]$	-	3375	-	k
Power dissipation	P_{MAX}	$T_{NTC} = 25^\circ\text{C}$	-	-	50	mW

Typical Performance

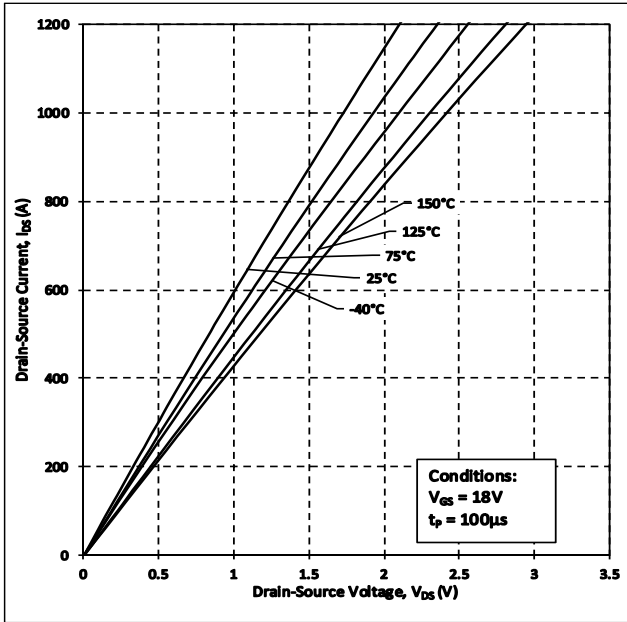


Figure 1. Output Characteristics for Various Temperatures

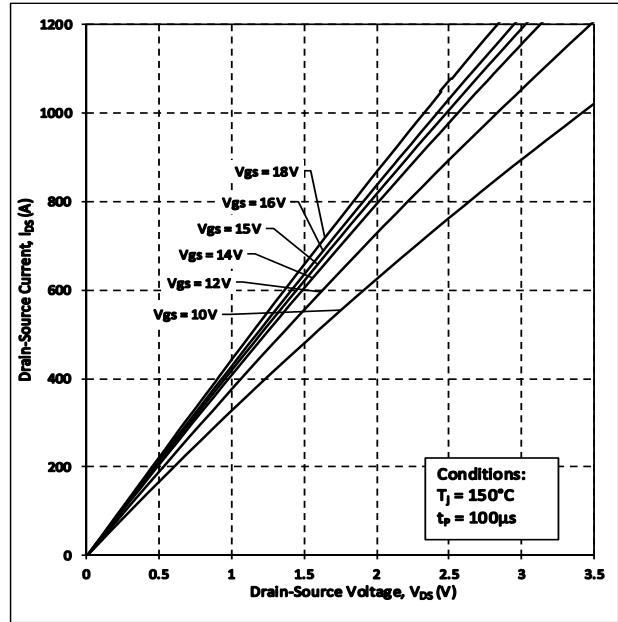


Figure 2. Output Characteristics $T_J = 150^\circ C$

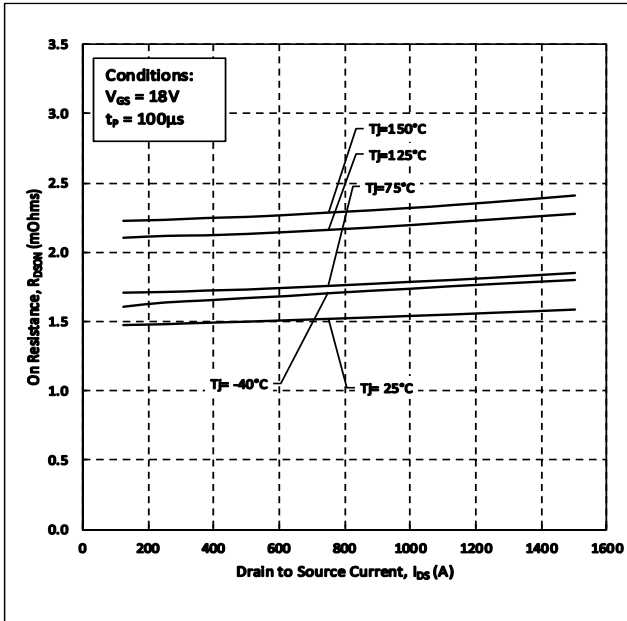


Figure 3. On-Resistance vs. Drain Current For Various Temperatures

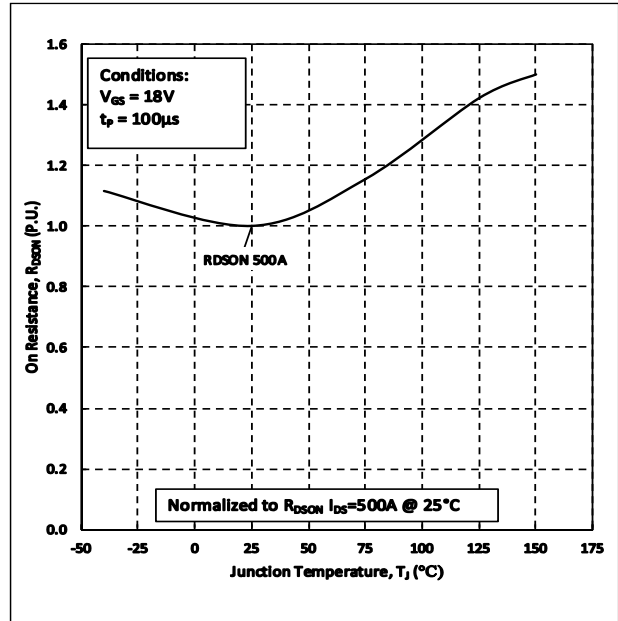


Figure 4. Normalized On-Resistance vs. Temperature

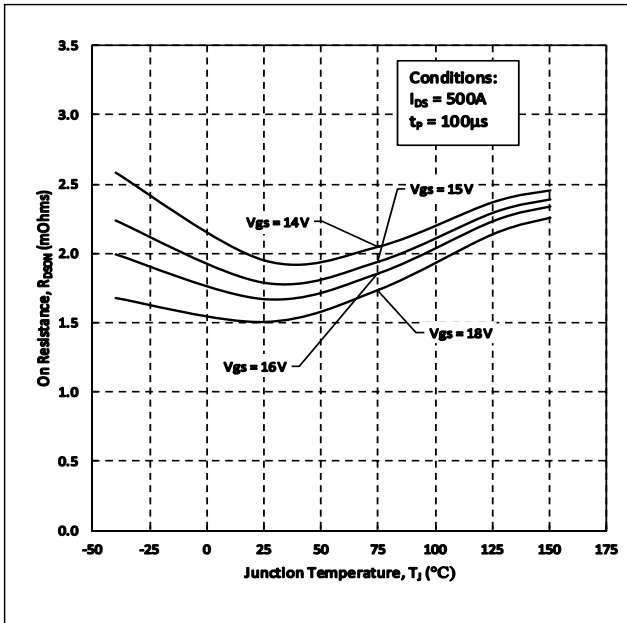


Figure 5. On-Resistance vs. Temperature For Various Gate Voltages

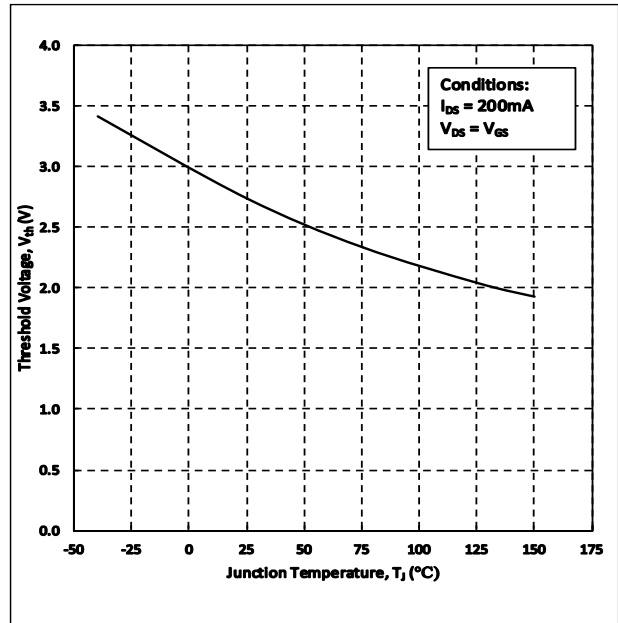


Figure 6. Threshold Voltage vs. Temperature

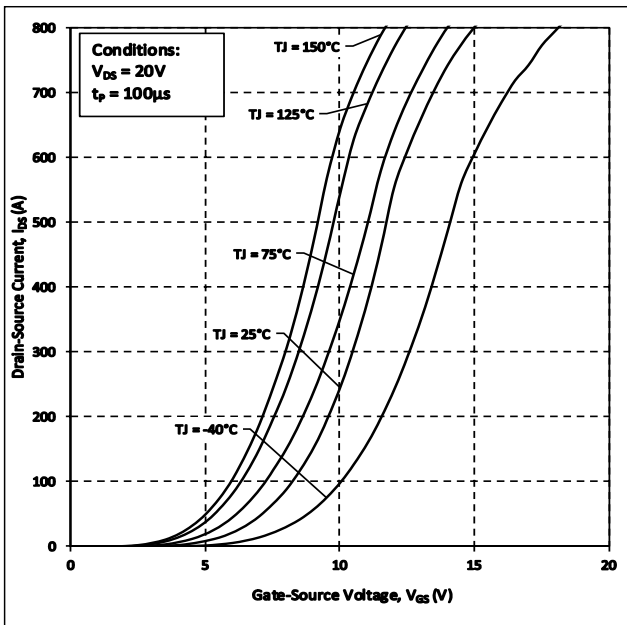


Figure 7. Transfer Characteristic for Various Junction Temperatures

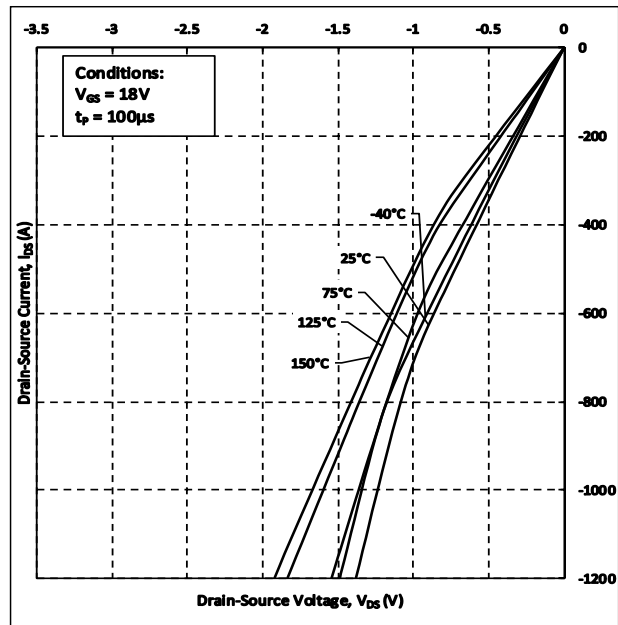


Figure 8. 3rd Quadrant Characteristics at $V_{GS} = 18V$

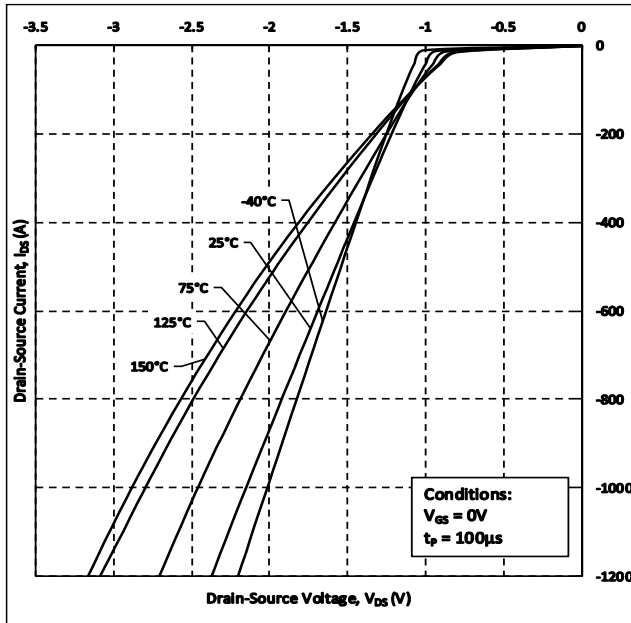


Figure 9. Body Diode Characteristics at $V_{GS} = 0V$

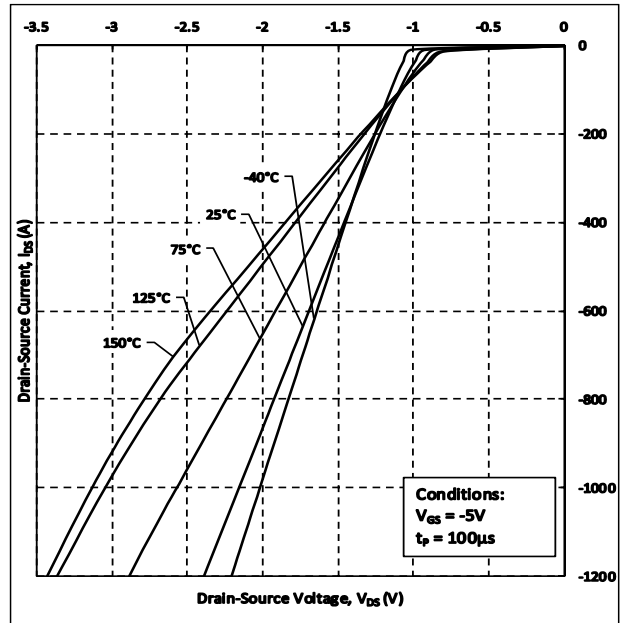


Figure 10. Body Diode Characteristics at $V_{GS} = -5V$

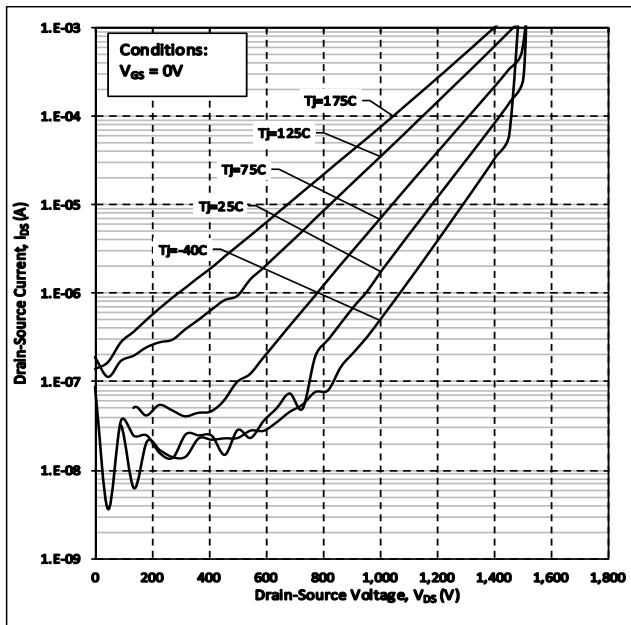


Figure 11. I_{DSS} vs Temperature

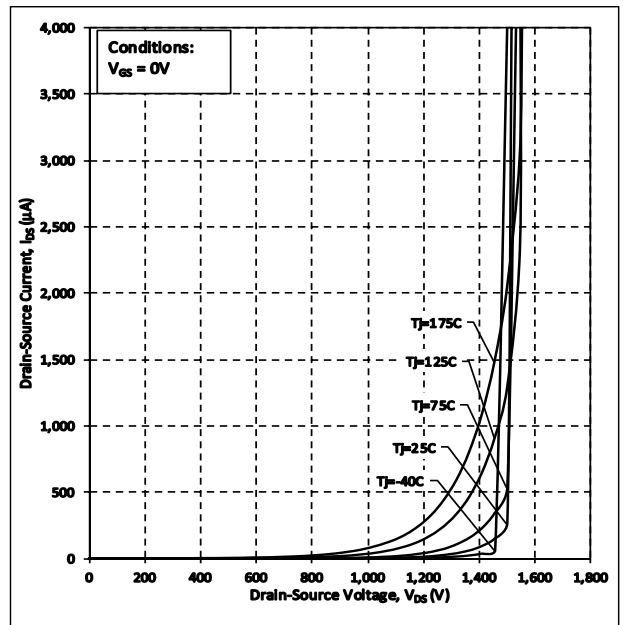


Figure 12. $BVDSS$ vs Temperature

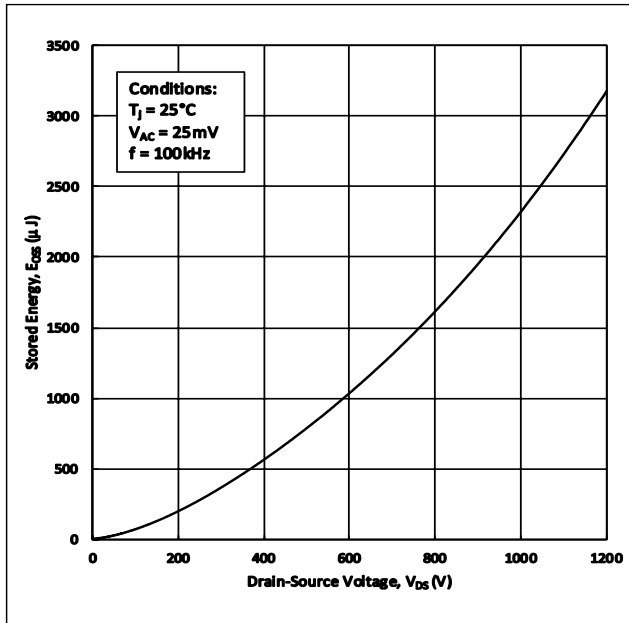


Figure 13. Output Capacitor Stored Energy

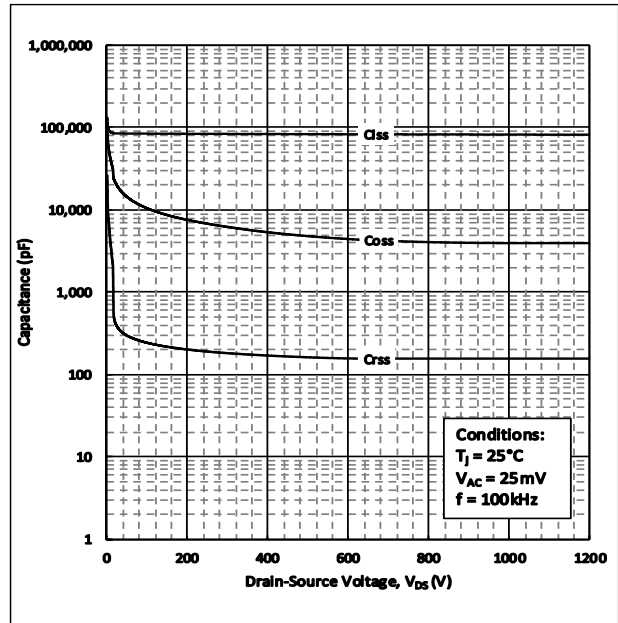


Figure 14. Capacitance vs. Drain-Source Voltage

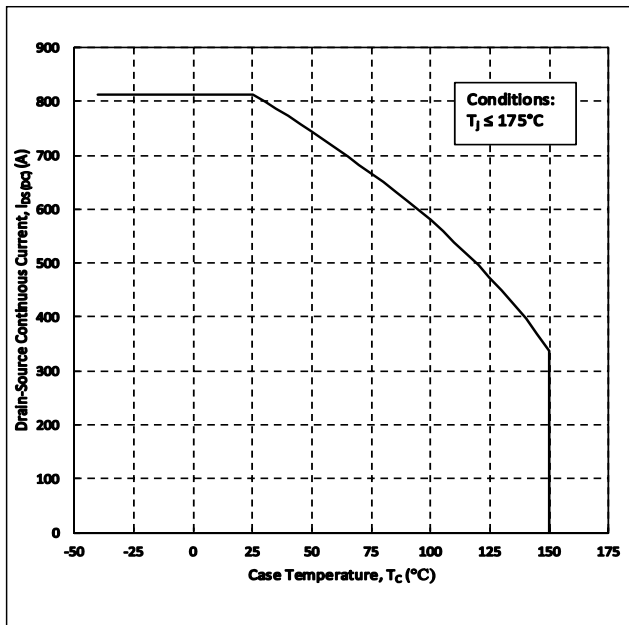


Figure 15. Continuous Drain Current Derating vs. Case Temperature

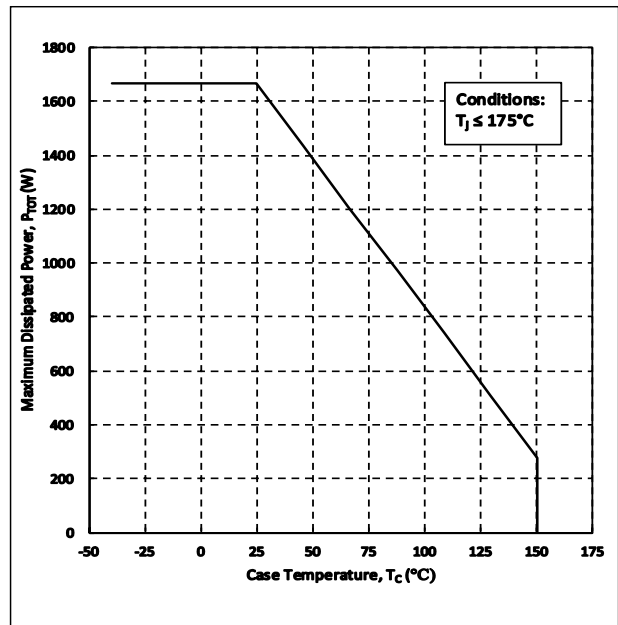


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

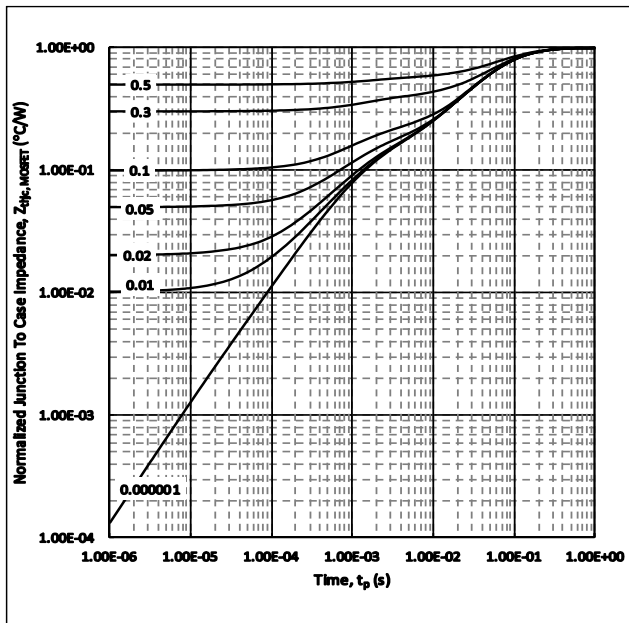


Figure 17. MOSFET Transient Thermal impedance (Junction to Case)

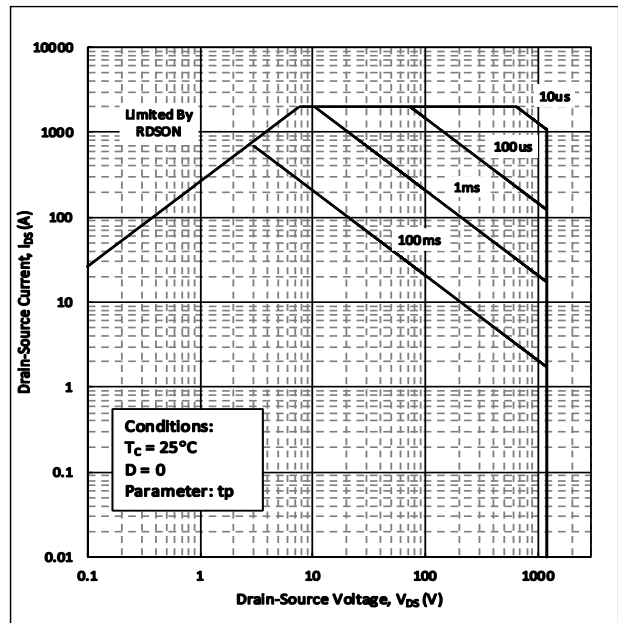


Figure 18. Safe Operating Area

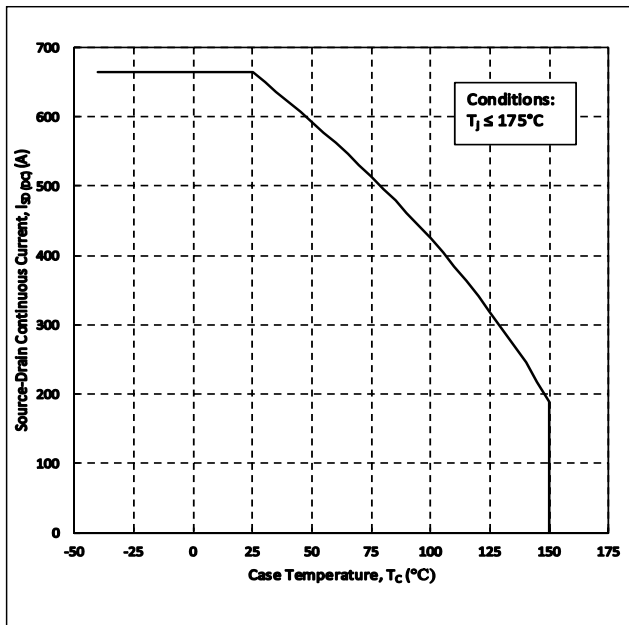


Figure 19. Continuous Source Current Derating vs. Case Temperature

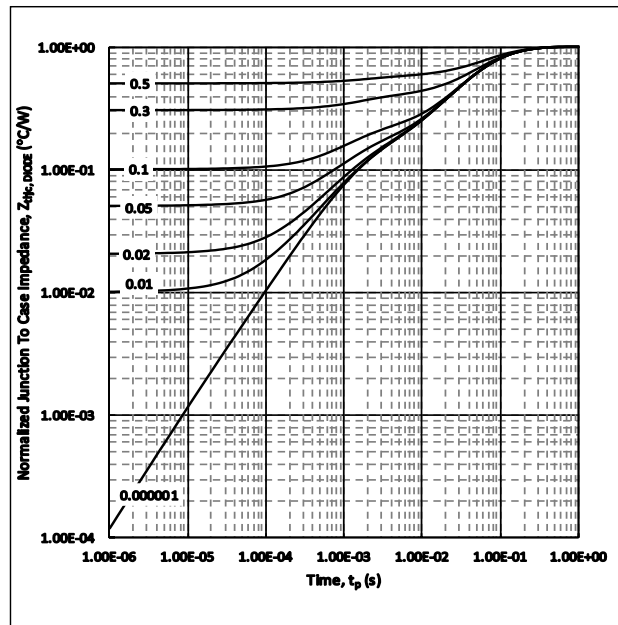


Figure 20. Diode Transient Thermal impedance (Junction to Case)

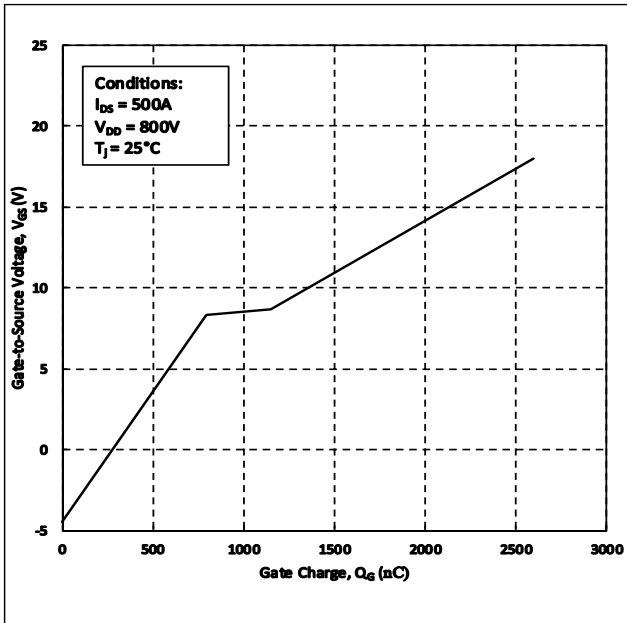


Figure 21. Gate Charge Characteristics

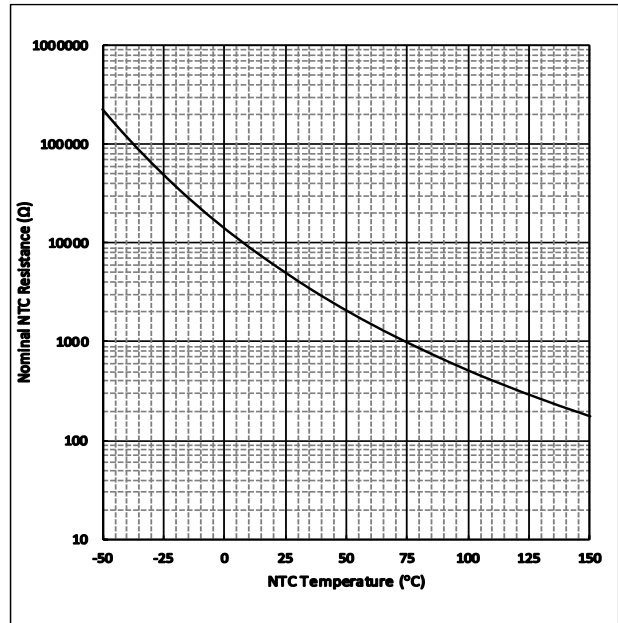


Figure 22. Nominal NTC Resistance vs. Temperature

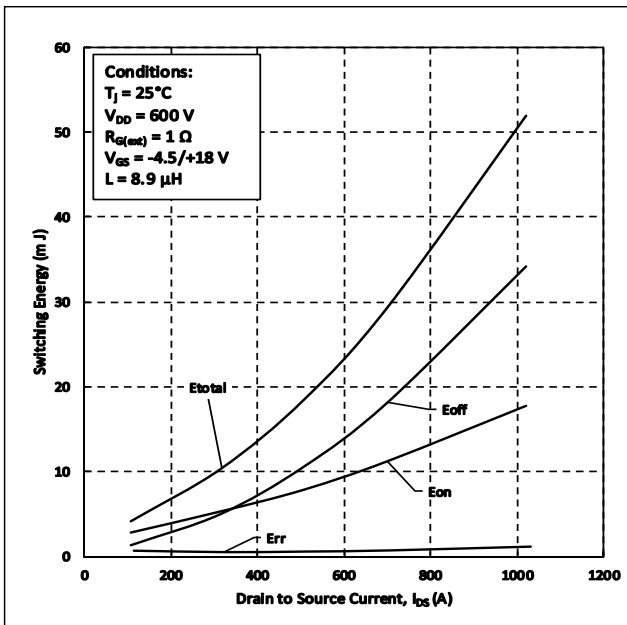


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (600V)

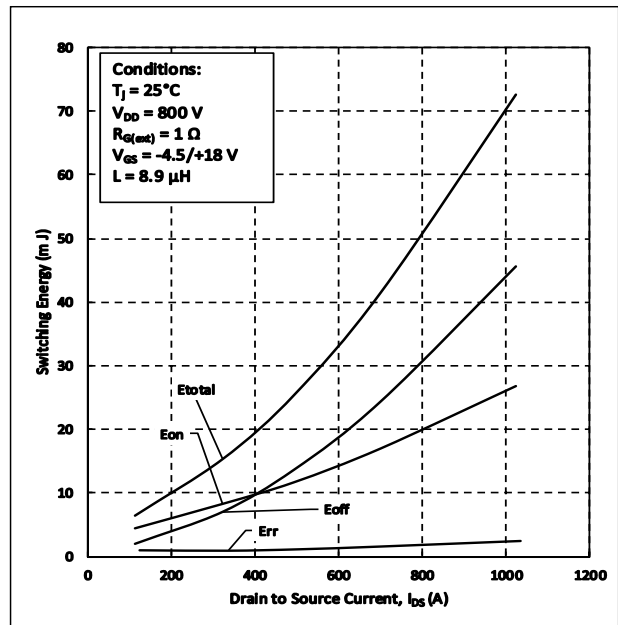


Figure 24. Clamped Inductive Switching Energy vs. Drain Current (800V)

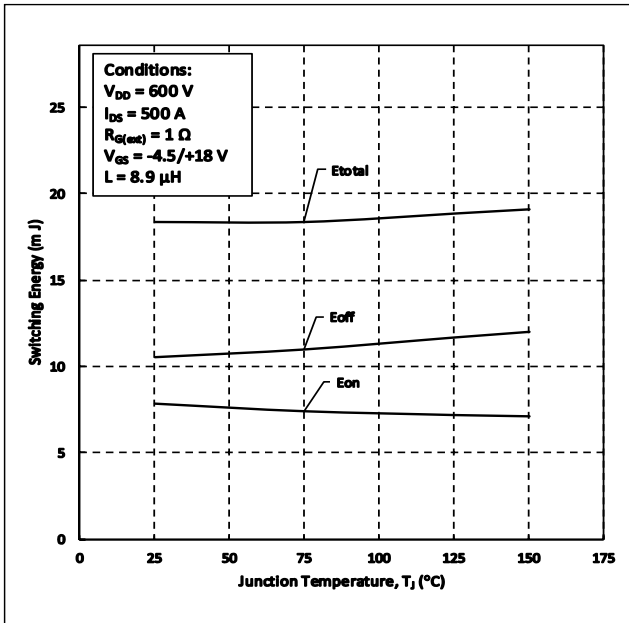


Figure 25. Clamped Inductive Switching Energy vs. Temperature

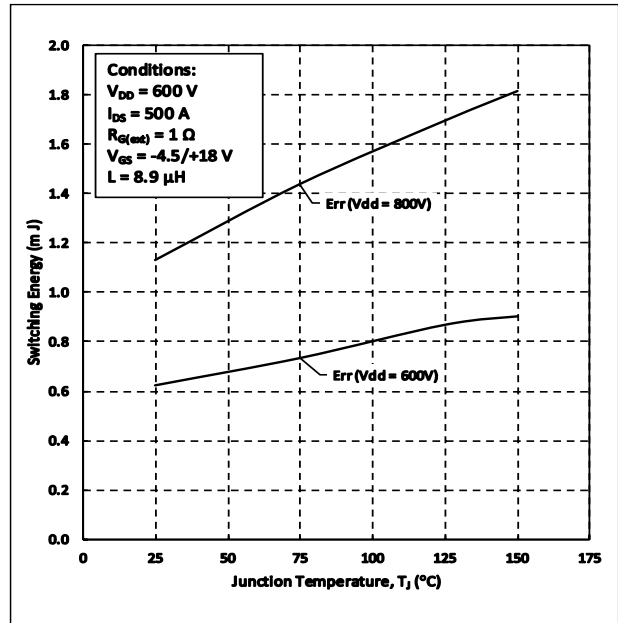


Figure 26. Reverse Recovery Energy vs. Temperature

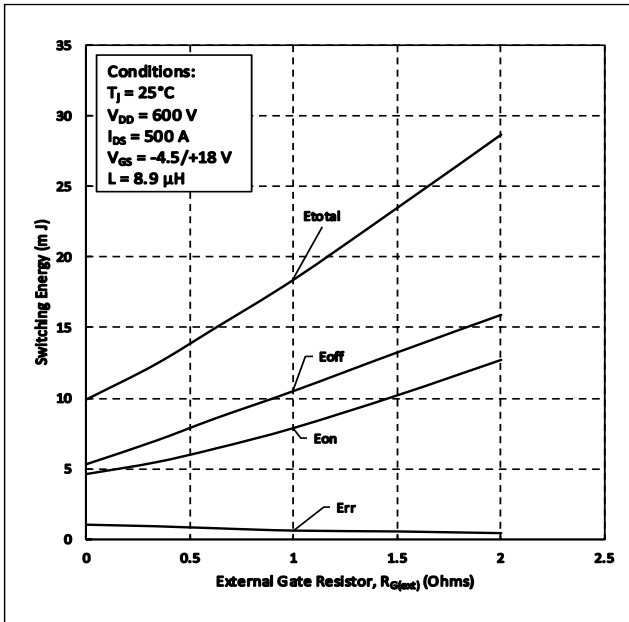


Figure 27. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

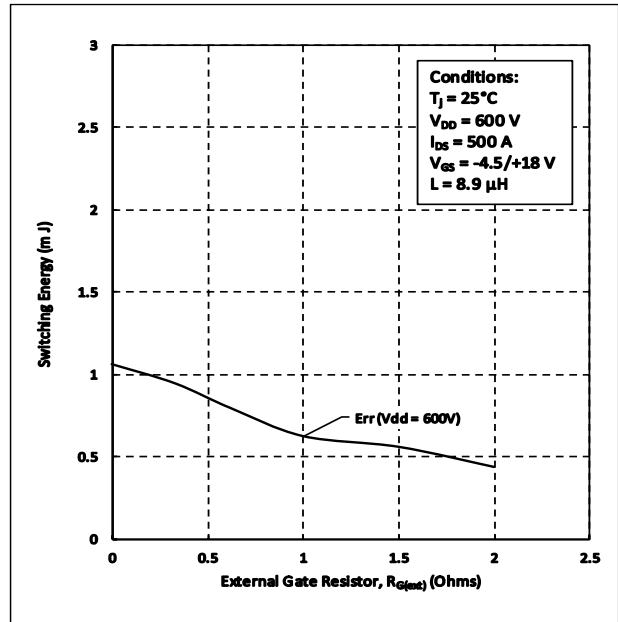


Figure 28. Reverse Recovery Energy vs. $R_{G(ext)}$

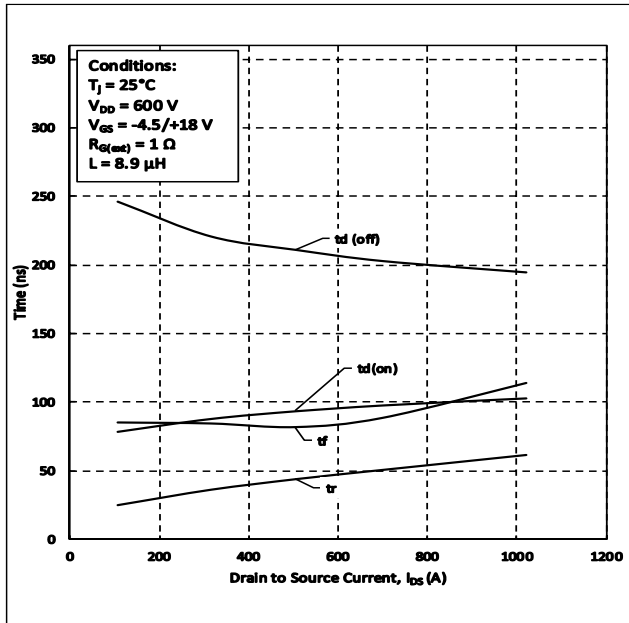


Figure 29. Switching Times vs. Drain Current

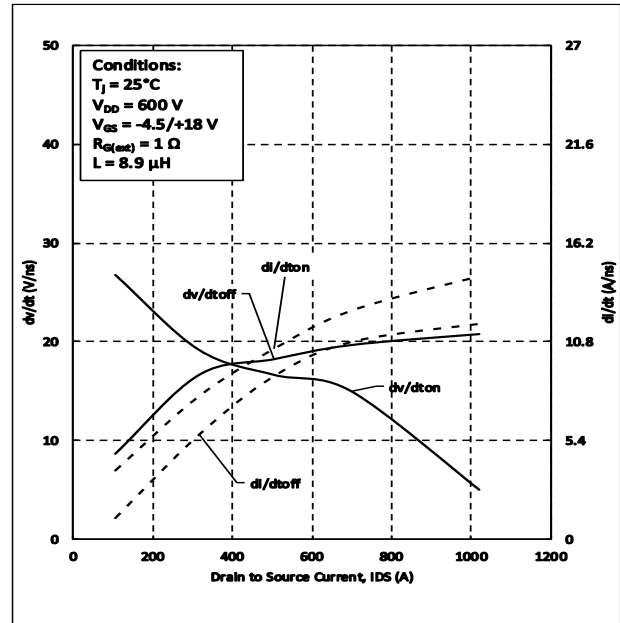


Figure 30. dv/dt and di/dt vs. Source Current

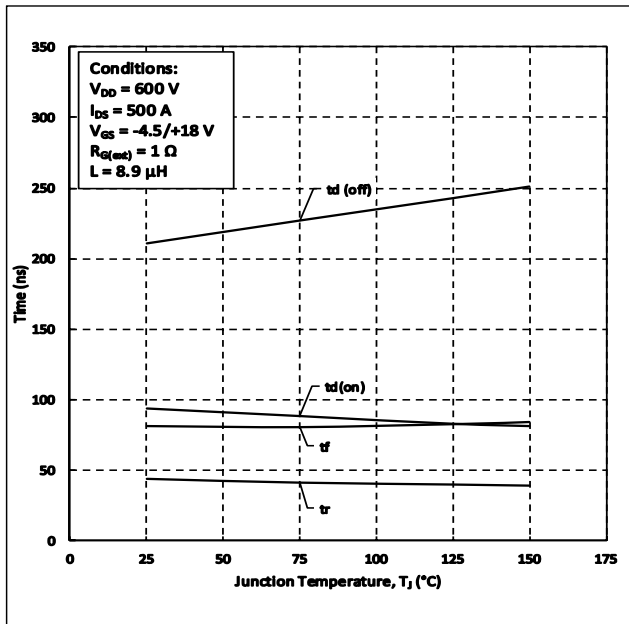


Figure 31. Switching Times vs. Temperature

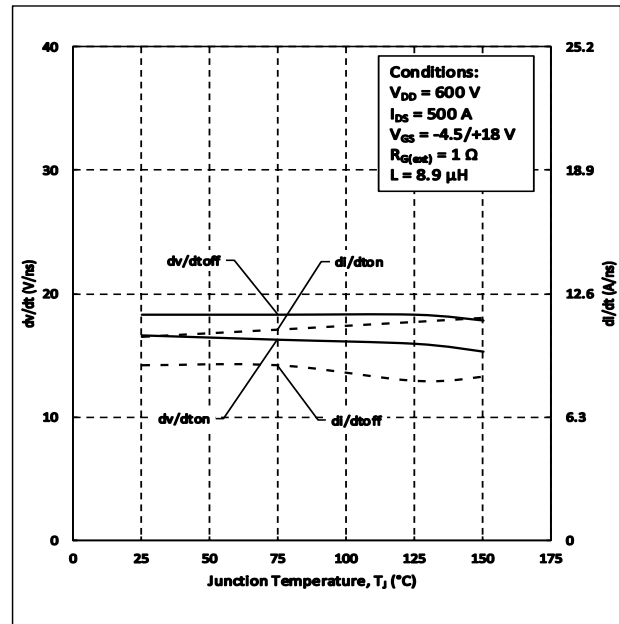


Figure 32. dv/dt and di/dt vs. Temperature

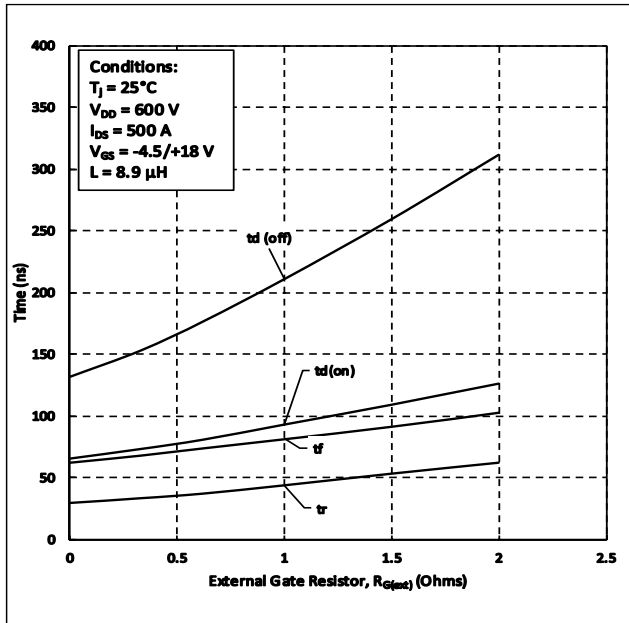


Figure 33. Switching Times vs. $R_{G(ext)}$

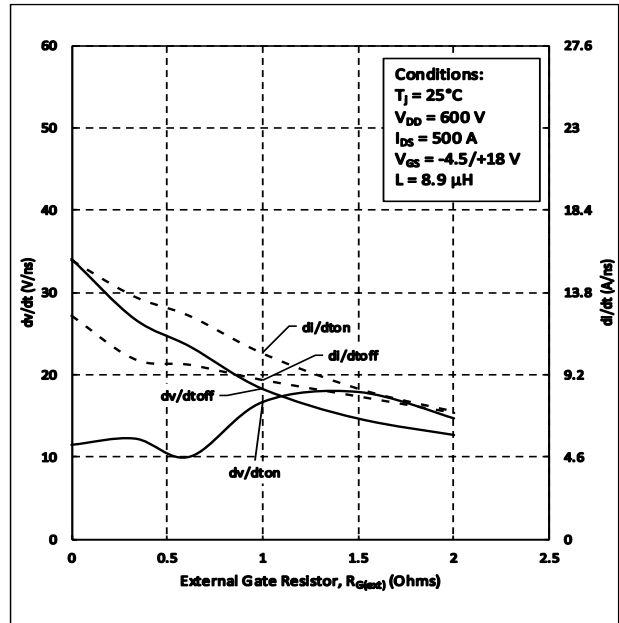


Figure 34. dv/dt and di/dt vs. $R_{G(ext)}$

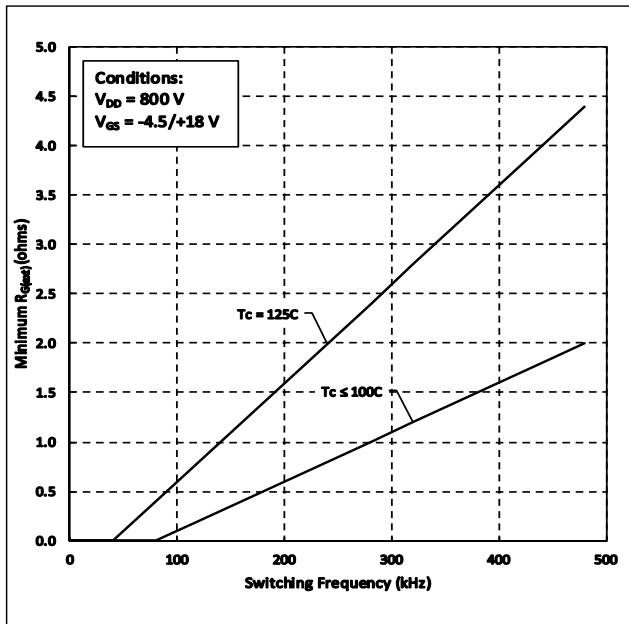


Figure 35. Frequency vs Minimum $R_{G(ext)}$



Figure 36. Reverse Recovery Definitions

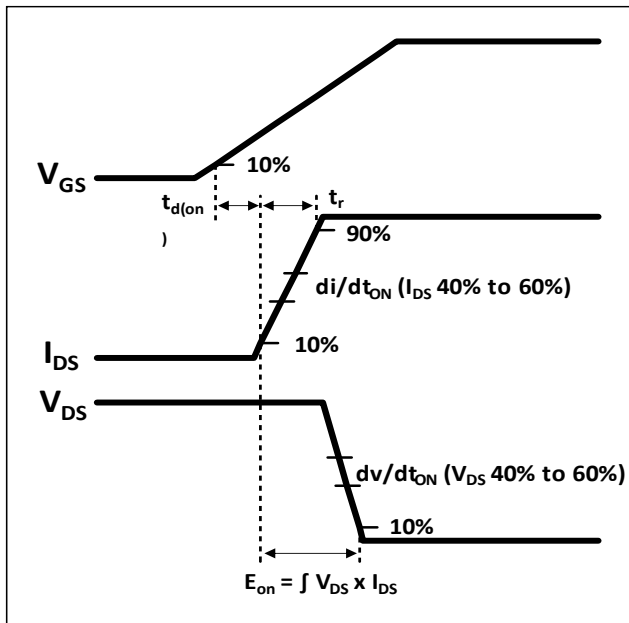


Figure 37. Turn-on Transient Definitions

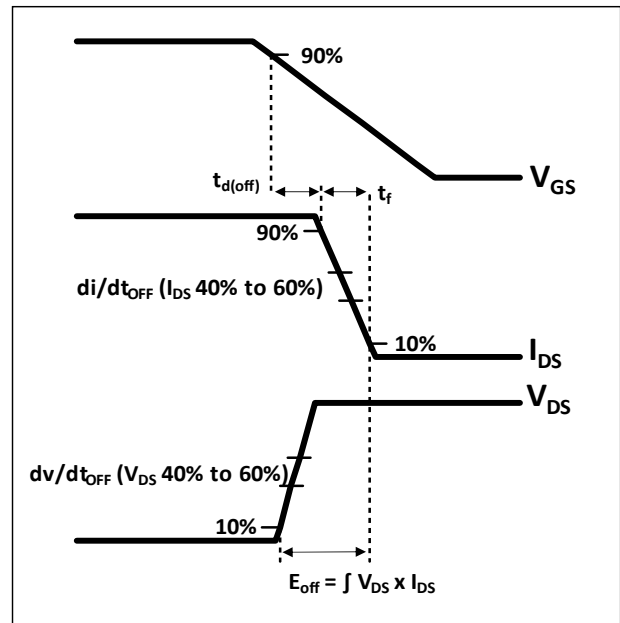
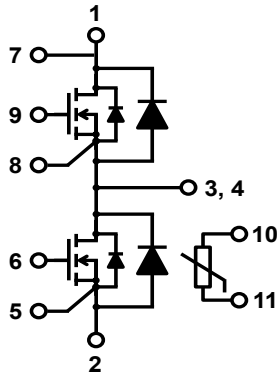


Figure 38. Turn-off Transient Definitions

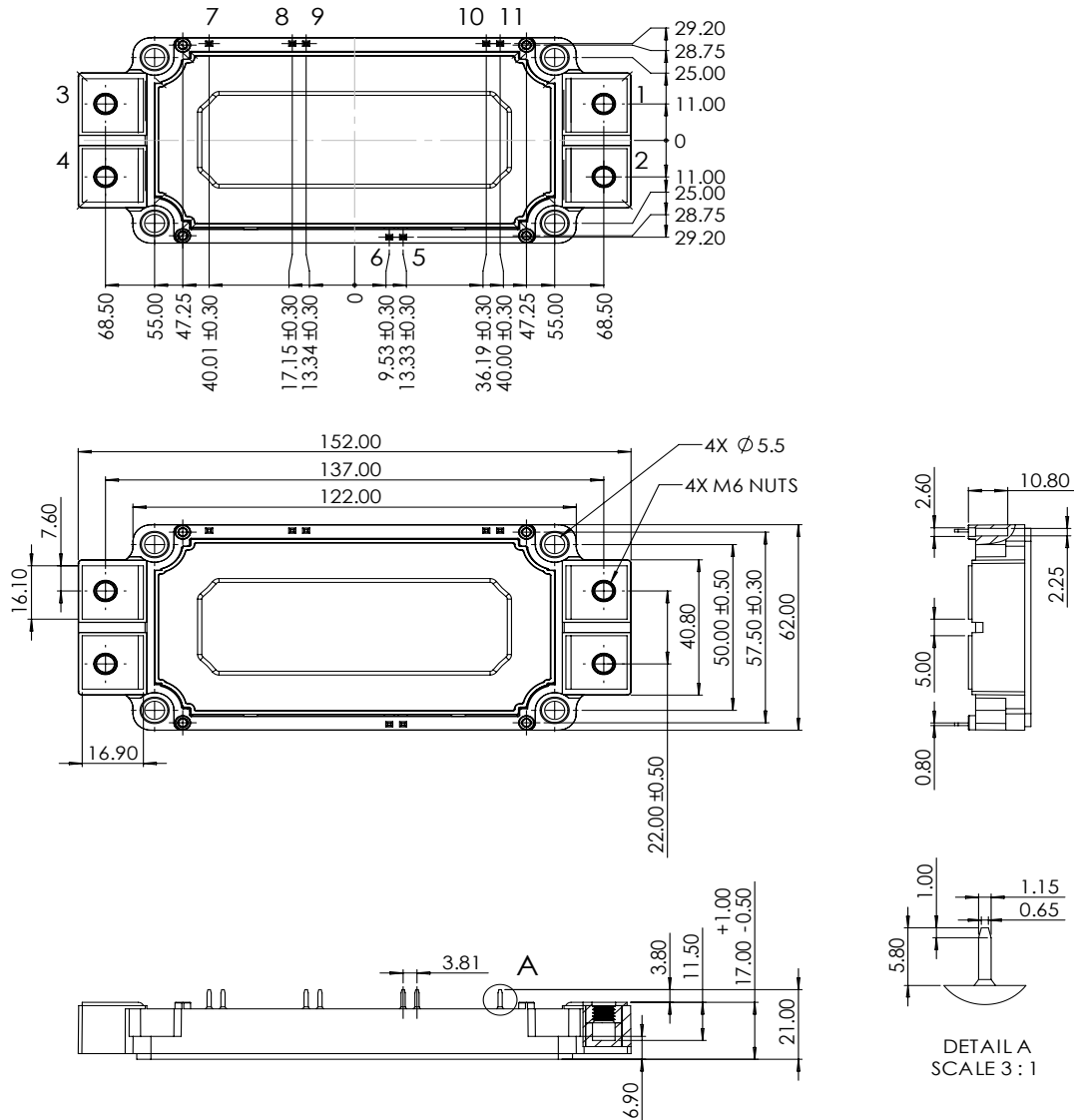
QSiC™ 1200V SiC Half-Bridge Module

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Pinout and Circuit Diagram



Package Dimensions (mm)



1200V SiC Half-Bridge Module

GCMS1P4B120S4B1

Revision History		
Date	Revision	Notes
3/20/2026	1.0	Initial release
3/27/2026	1.1	Removed extra text

Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2015/863 (RoHS3), as implemented July, 2019. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

REACH Compliance

REACH substances of high concern (SVHC) information is available for this product. Since the European Chemicals Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at SemiQ Headquarters in Lake Forest, California to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request. SemiQ Inc., reserves the right to make changes to the product specifications and data in this document without notice. SemiQ products are sold pursuant to SemiQ's terms and conditions of sale in place at the time of order acknowledgement.

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